

	L #	Hits	Search Text	DBs
1	L1	164133	"438"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
2	L2	6480	1 and (TFT or (thin near film near transistor) or (thin-film near transistor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
3	L3	6	2 and (dop\$3 or introduc\$3) near (source or drain) near (laser or irradiat\$3 or KrF)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
4	L4	408	zhang-hongyong.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
5	L5	0	4 and (dop\$3 or introduc\$3 or implant\$3) near (source or drain) near (laser or irradiat\$3 or KrF)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
6	L6	20569	(TFT or (thin near film near transistor) or (thin-film near transistor)).ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
7	L7	3	6 and (dop\$3 or introduc\$3 or implant\$3) near (source or drain) near (laser or irradiat\$3 or KrF)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
8	L8	84545	(TFT or (thin near film near transistor) or (thin-film near transistor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
9	L1 0	0	9 and decompos\$3 near (electrical near energy)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
10	L9	8	8 and (dop\$3 or introduc\$3 or implant\$3) near (source or drain) near (laser or irradiat\$3 or KrF)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB